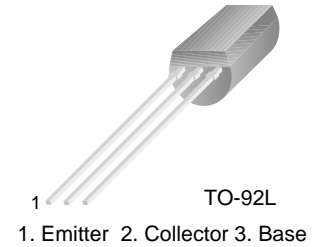


■■ APPLICATION: High Voltage Switching Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CBO</sub>	200	V
Collector-emitter voltage	V <sub>CEO</sub>	150	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	50	mA
Collector Power Dissipation	P <sub>C</sub>	800	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	70		240		V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA
Collector Cut-off Current	I <sub>CBO</sub>			0.1	μA	V <sub>CB</sub> = 200V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			0.1	μA	V <sub>EB</sub> = 5 V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200			V	I <sub>C</sub> = 0.05mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	150			V	I <sub>C</sub> = 1 mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5			V	I <sub>E</sub> = 0.05 mA, I <sub>C</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			0.5	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>			1.0	V	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1 mA
Gain bandwidth product	f <sub>T</sub>	80	120		MHz	I <sub>C</sub> = 5 mA, V <sub>CE</sub> = 30V
Common Base Output Capacitance	C <sub>ob</sub>			5	PF	V <sub>CB</sub> = 10 V, I <sub>E</sub> =0, f = 1 MHz

■■ hFE Classification And Marking

Classification	O	Y
h <sub>FE</sub>	70~140	120~240